## SPTECH Silicon PNP Power Transistor

### MJW0302G

#### **DESCRIPTION**

· High Collector-Emitter Breakdown

Voltage-: V<sub>(BR)CEO</sub>=250V(Min)

- · Good Linearity of hFE
- Complement to Type NJW0281G

#### **APPLICATIONS**

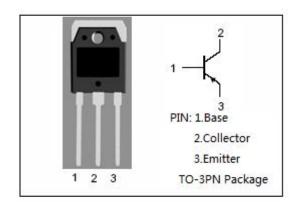
 Designed for high fidelity audio amplifier and other linear applications

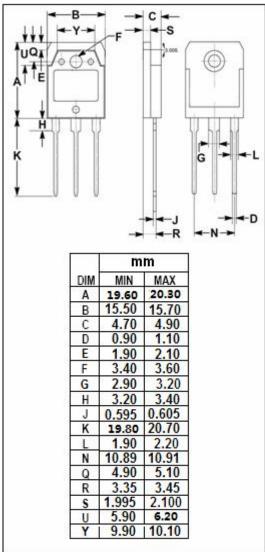
### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage -250		V	
V <sub>CEO</sub>	Collector-Emitter Voltage	-250	V	
V <sub>CEX</sub>	Collector-Emitter Voltage V <sub>EB</sub> = 5V	-250	V	
V <sub>EBO</sub>	Emitter-Base Voltage -		V	
Ic	Collector Current-Continuous -15		Α	
I <sub>CM</sub>	Collector Current-Peak	-30	Α	
I <sub>B</sub>	Base Current-Continuous	Current-Continuous -1.5		
P <sub>T</sub>	Total Power Dissipation @ T <sub>C</sub> =25℃	150	W	
TJ	Junction Temperature 150		$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$ C	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case		°C/W





# **SPTECH Product Specification**

# SPTECH Silicon PNP Power Transistor

MJW0302G

### **ELECTRICAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =- 100mA; I <sub>B</sub> = 0	-250			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -10A; I <sub>B</sub> =- 1A			-0.6	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	Ic= -8A;V <sub>CE</sub> = -5V			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> =- 250V			-50	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> =- 250V			-50	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> =- 5V			-5	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.1A; V <sub>CE</sub> =-5V	75		150	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V	75		150	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = -3A; V <sub>CE</sub> = -5V	75		150	
h <sub>FE-4</sub>	DC Current Gain	I <sub>C</sub> =- 5A; V <sub>CE</sub> = -5V	45			
h <sub>FE-5</sub>	DC Current Gain	I <sub>C</sub> =- 8A; V <sub>CE</sub> = -5V	15			

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